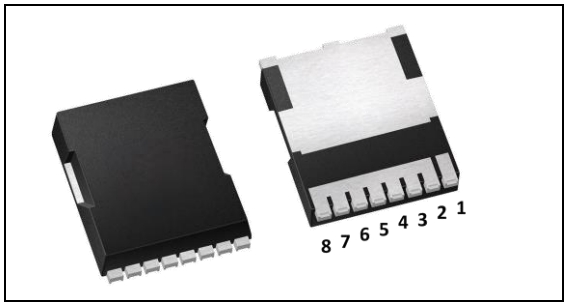
N-Channel 100 V MOSFET

Product summary

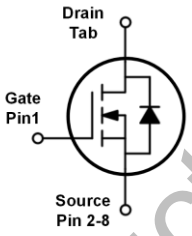
V_{DS} (V)	$R_{DS(on),max}$ (mΩ)	I_D (A)
100	1.5 @ V_{GS} = 10V	330 (1)

TOLL



Features

- Low $R_{DS(on)}$ SGT technology
- Low thermal impedance
- Fast switching speed
- 100% avalanche tested



RoHS COMPLIANT

Pb-Free

HF

Applications

- DC/DC conversion
- Power switch

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1. Maximum ratings

Absolute maximum ratings (T_A = 25℃ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source voltage		V_{DS}	100	V
Gate-source voltage		V_{GS}	±20	
Continuous drain current	T_C=25℃ (1)	I_D	330	A
	T_C=100℃		246	
	T_A=25℃ (4)		33	
Pulsed drain current(2)		$I_{D,pulse}$	1320	
Avalanche energy, single pulse(3)		E_{AS}	540	mJ
Power dissipation	T_C=25℃	P_D	431	W
	T_A=25℃ (4)		3.1	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to 150	℃

2. Thermal resistance ratings

Thermal resistance ratings				
Parameter		**Symbol**	**Max.**	**Unit**
Thermal resistance, junction-to-case	Steady state	$R_{\theta JC}$	0.29	°C/W
Thermal resistance, junction-to-ambient (4)	Steady state	$R_{\theta JA}$	40	

3. Electrical characteristics

Electrical characteristics (T_J = 25°C unless otherwise noted)						
Parameter	**Symbol**	**Test conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static parameter						
Drain to source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 1 mA	100			V
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	2.2	3	3.8	V
Gate-body leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} = 100 V, V_{GS} = 0 V			1	µA
Drain-source on-resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 100 A		1.2	1.5	mΩ
Forward transconductance(5)	g_{fs}	V_{DS} = 5 V, I_D = 100 A		260		S
Gate resistance	R_g	f = 1 MHz		1		Ω
Dynamic(5)						
Total gate charge	Q_g	V_{DS} = 50 V, I_D = 100 A, V_{GS} = 10 V		260		nC
Gate-source charge	Q_{gs}			75		
Gate-drain charge	Q_{gd}			76		
Turn-on delay time	$t_{d(on)}$	V_{DS} = 50 V, I_D = 100 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		81		ns
Rise time	t_r			178		
Turn-off delay time	$t_{d(off)}$			167		
Fall time	t_f			68		
Input capacitance	C_{iss}	V_{DS} = 50 V, V_{GS} = 0 V, f = 1 MHz		15800		pF
Output capacitance	C_{oss}			1930		
Reverse transfer capacitance	C_{rss}			75		
Reverse Diode Characteristics(5)						
Diode forward voltage	V_{SD}	V_{GS} = 0 V, I_F = 100 A		0.85	1.1	V
Reverse recovery time	t_{rr}	V_{DS} = 50 V, I_F = 100 A, di/dt = 100 A/µs		92		ns
Reverse recovery charge	Q_{rr}			200		nC

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Notes

(1) Package limited.

(2) Pulse width limited by maximum junction temperature.

(3) V_{DS} = 75 V, V_{GS} = 10 V, L = 0.3 mH.

(4) $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5x1.5 in. board of FR-4 material.

(5) Guaranteed by design, not subject to production testing.

4. Electrical characteristics diagrams

Fig.1 Typ. transfer characteristics

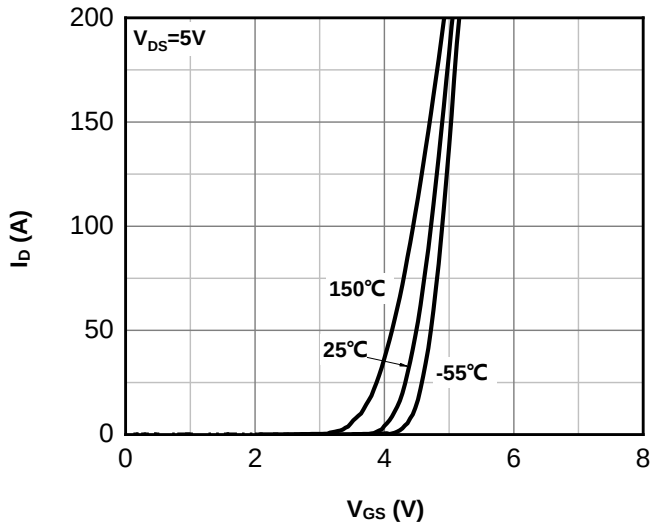

Fig.2 Typ. output characteristics

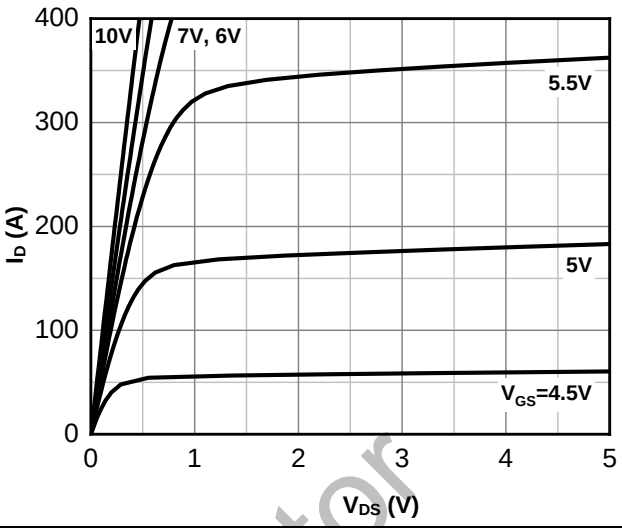

Fig.3 Normalized on-resistance vs drain current

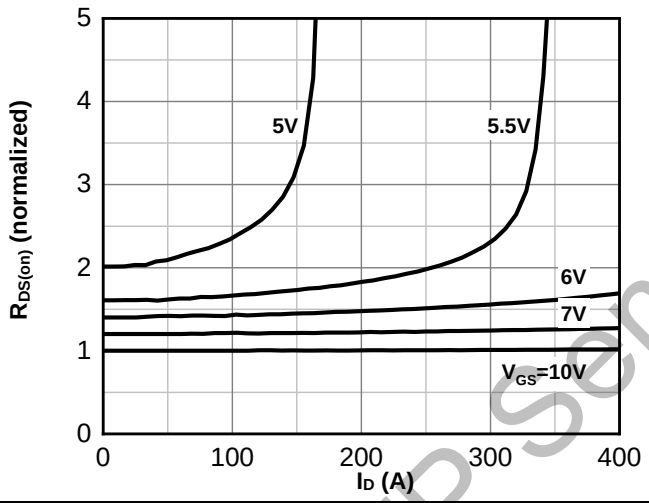

Fig.4 Typ. on-resistance vs gate-source voltage

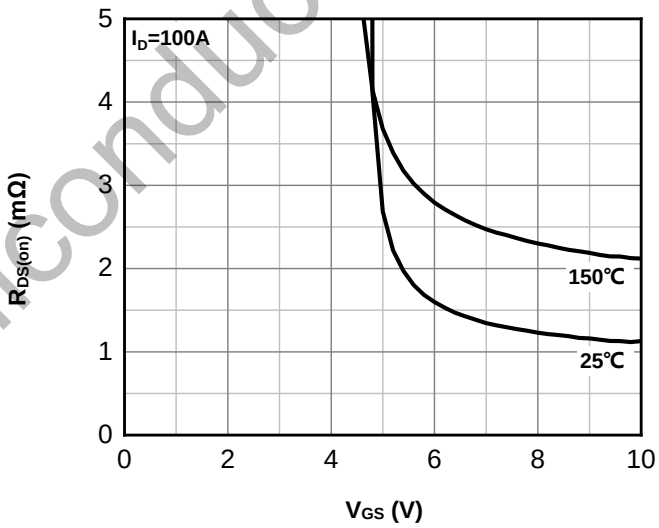

Fig.5 Normalized on-resistance vs junction temperature

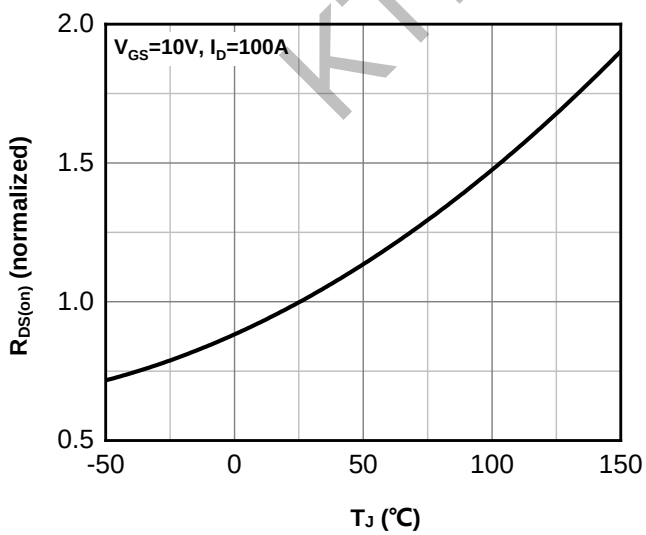

Fig.6 Typ. gate charge

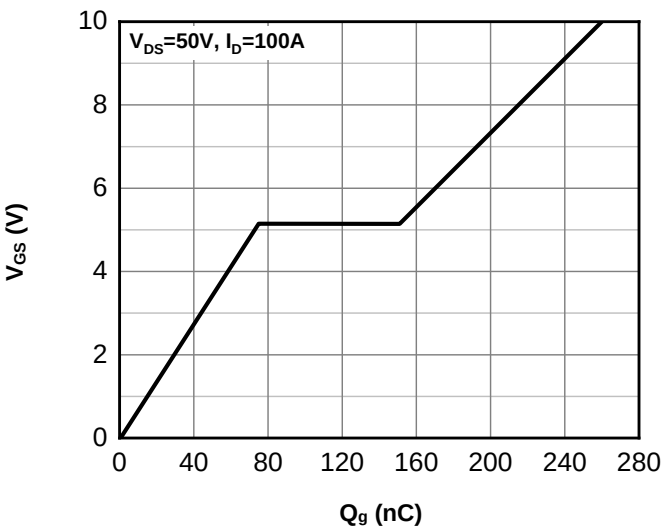

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Fig.7 Typ. forward characteristics of body diode

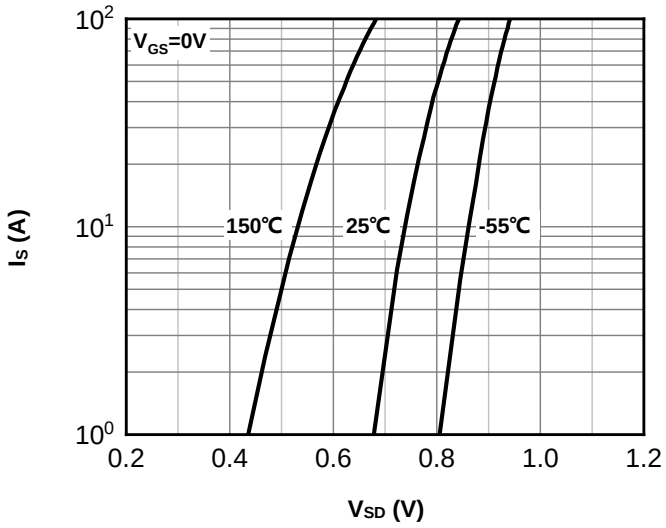

Fig.8 Safe operating area

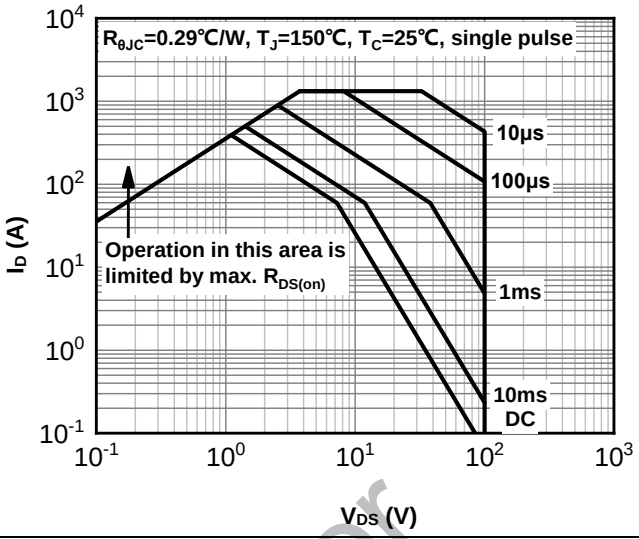

Fig.9 Typ. Capacitance

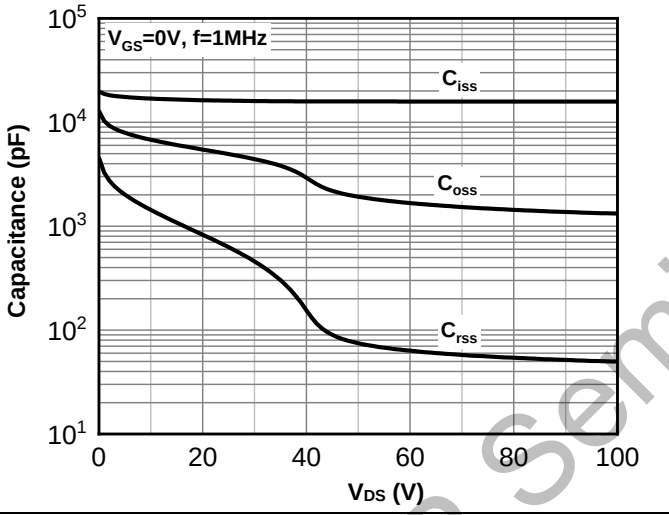

Fig.10 Single pulse maximum power dissipation

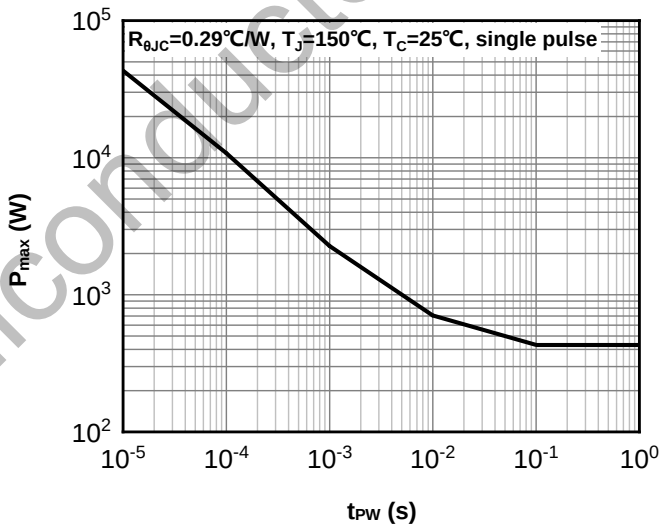

Fig.11 Max. power dissipation vs case temperature

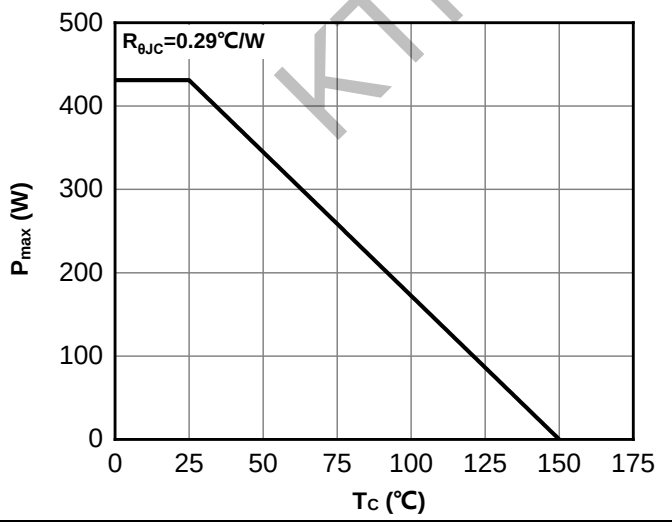

Fig.12 Max. continuous drain current vs case temperature

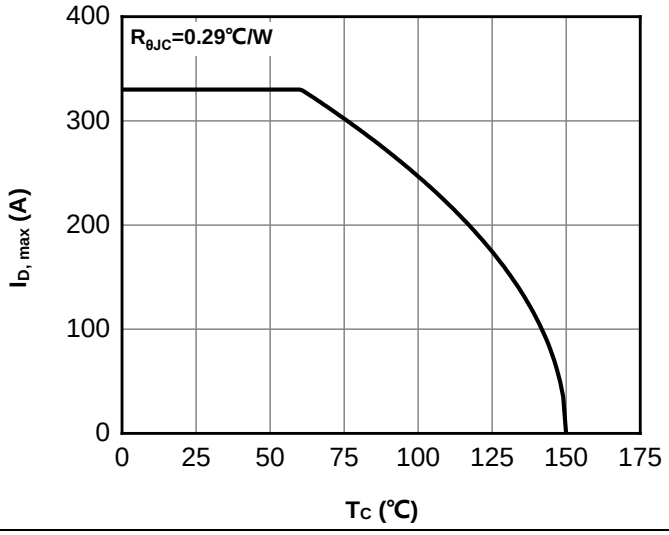

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Fig.13 Normalized $V_{(BR)DSS}$ vs junction temperature

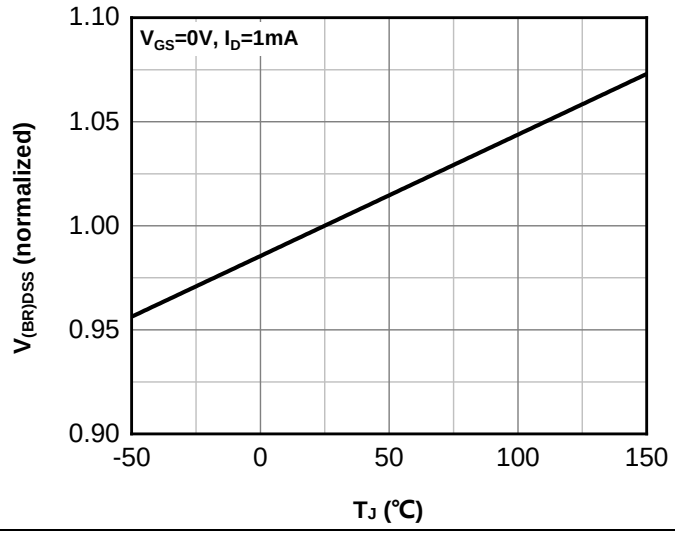


Fig.14 Normalized $V_{GS(th)}$ vs junction temperature

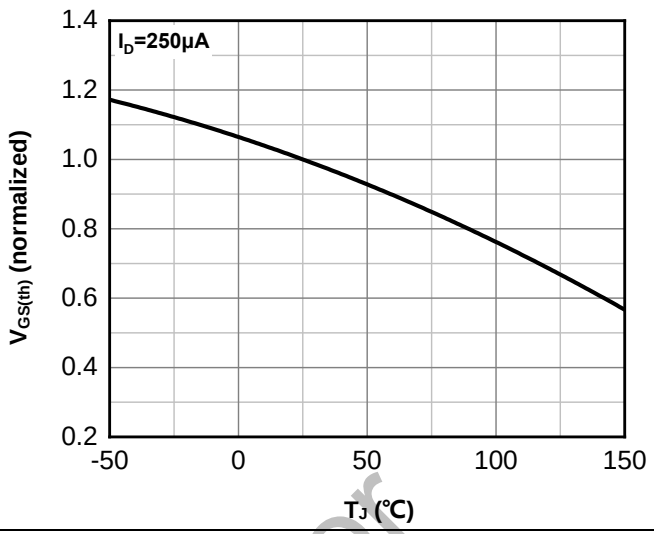
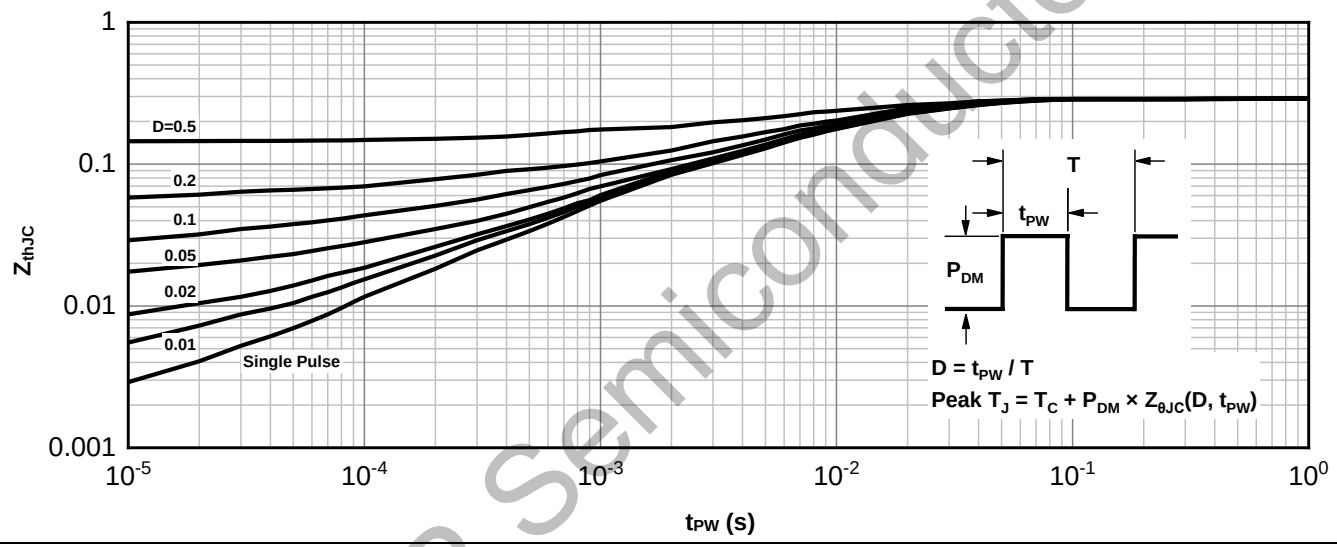


Fig.15 Transient thermal impedance from junction to case



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